

6-Mbit (256K X 24) Static RAM

Features

- High speed

 □ t_{AA} = 10 ns
- Low active power
 □ I_{CC} = 175 mA at f = 100 MHz
- Low CMOS standby power
 □ I_{SB2} = 25 mA
- Operating voltages of 3.3 ± 0.3 V
- 2.0 V data retention
- Automatic power-down when deselected
- Transistor-transistor logic (TTL) compatible inputs and outputs
- Easy memory expansion with \overline{CE}_1 , CE_2 , and \overline{CE}_3 features
- Available in Pb-free standard 119-Ball PBGA

Functional Description

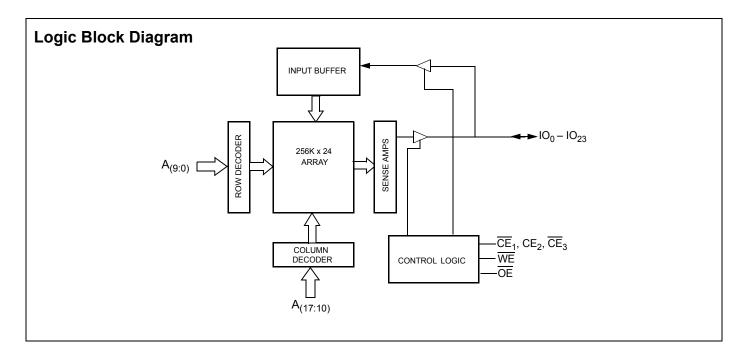
The CY7C1034DV33 is a high performance CMOS static RAM organized as 256K words by 24 bits. This device has an automatic power-down feature that significantly reduces power consumption when deselected.

To write to the device, enable the chip $(\overline{CE}_1 LOW, CE_2 HIGH,$ and $\overline{CE}_3 LOW)$ while forcing the Write Enable (\overline{WE}) input LOW.

To read from the device, enable the chip by taking \overline{CE}_1 LOW, CE_2 HIGH, and \overline{CE}_3 LOW, while forcing the Output Enable (\overline{OE}) LOW and the Write Enable (\overline{WE}) HIGH. See the Truth Table on page 7 for a complete description of Read and Write modes.

The 24 IO pins (IO $_0$ to IO $_{23}$) are <u>placed</u> in a high impedanc<u>e state</u> when the device is deselected (CE $_1$ HIGH, CE $_2$ LOW, or CE $_3$ HIGH) or <u>when</u> the output enable (OE) is HIGH d<u>uring</u> a write operation. (CE $_1$ LOW, CE $_2$ HIGH, CE $_3$ LOW, and WE LOW).

For a complete list of related documentation, click here.





Selection Guide

Description	-10	Unit
Maximum access time	10	ns
Maximum operating current	175	mA
Maximum CMOS standby current	25	mA

Pin Configuration

Figure 1. 119-Ball PBGA Top View [1]

	1	2	3	4	5	6	7
Α	NC	Α	Α	Α	Α	Α	NC
В	NC	Α	Α	CE ₁	Α	Α	NC
С	IO ₁₂	NC	CE ₂	Α	CE ₃	NC	IO ₀
D	IO ₁₃	V_{DD}	V _{SS}	V _{SS}	V _{SS}	V_{DD}	IO ₁
E	1O ₁₄	V_{SS}	V_{DD}	V _{SS}	V_{DD}	V_{SS}	IO ₂
F	IO ₁₅	V_{DD}	V _{SS}	V _{SS}	V _{SS}	V_{DD}	IO ₃
G	IO ₁₆	V_{SS}	V_{DD}	V _{SS}	V_{DD}	V_{SS}	IO ₄
Н	1O ₁₇	V_{DD}	V _{SS}	V _{SS}	V _{SS}	V_{DD}	1O ₅
J	NC	V_{SS}	V_{DD}	V _{SS}	V_{DD}	V_{SS}	NC
K	IO ₁₈	V_{DD}	V_{SS}	V_{SS}	V_{SS}	V_{DD}	1O ₆
L	IO ₁₉	V_{SS}	V_{DD}	V _{SS}	V_{DD}	V_{SS}	107
M	1O ₂₀	V_{DD}	V _{SS}	V _{SS}	V_{SS}	V_{DD}	IO ₈
N	IO ₂₁	V_{SS}	V_{DD}	V _{SS}	V_{DD}	V_{SS}	IO ₉
Р	1O ₂₂	V_{DD}	V _{SS}	V _{SS}	V _{SS}	V_{DD}	IO ₁₀
R	IO ₂₃	NC	NC	NC	NC	NC	IO ₁₁
T	NC	Α	Α	WE	Α	Α	NC
U	NC	Α	Α	ŌĒ	Α	Α	NC

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Note
1. NC pins are not connected on the die.



Maximum Ratings

Exceeding maximum ratings may impair the useful life of the device. These user guidelines are not tested. Storage Temperature-65 °C to +150 °C Ambient Temperature with Supply Voltage on $\rm V_{CC}$ Relative to GND $^{[2]}..-0.5$ V to +4.6 V DC Voltage Applied to Outputs in High Z State $^{[2]}.....-0.5$ V to V $_{\rm CC}$ + 0.5 V

DC Input Voltage [2]	0.5 V to V _{CC} + 0.5 V
Current into Outputs (LOW)	20 mA
Static Discharge Voltage	>2001 V
(MIL-STD-883, Method 3015)	
Latch up Current	>200 mA

Operating Range

Range	Ambient Temperature	V _{cc}	
Industrial	–40 °C to +85 °C	3.3 V \pm 0.3 V	

DC Electrical Characteristics

Over the operating range

Davamatar	Description	Test Conditions [3]	-	Unit	
Parameter	Description	rest Conditions 1-7	Min	Max	Unit
V _{OH}	Output HIGH voltage	Min V_{CC} , $I_{OH} = -4.0 \text{ mA}$	2.4		V
V _{OL}	Output LOW voltage	$Min V_{CC}, I_{OL} = 8.0 mA$		0.4	V
V _{IH}	Input HIGH voltage		2.0	V _{CC} + 0.3	V
V _{IL} [2]	Input LOW voltage		-0.3	0.8	V
I _{IX}	Input leakage current	$GND \le V_{IN} \le V_{CC}$	– 1	+1	μΑ
I _{OZ}	Output leakage current	$GND \le V_{OUT} \le V_{CC}$, output disabled	– 1	+1	μΑ
I _{CC}	V _{CC} operating supply current	$\begin{aligned} &\text{Max V}_{\text{CC}}, \text{f = f}_{\text{MAX}} = 1/\text{t}_{\text{RC}}, \\ &\text{I}_{\text{OUT}} = 0 \text{mA CMOS levels} \end{aligned}$		175	mA
I _{SB1}	Automatic CE power-down current — TTL inputs	$\begin{aligned} &\text{Max V}_{\text{CC}}, \overline{\text{CE}}_{1}, \overline{\text{CE}}_{3} \geq \text{V}_{\text{IH}}, \text{CE}_{2} \leq \text{V}_{\text{IL}}, \\ &\text{V}_{\text{IN}} \geq \text{V}_{\text{IH}} \text{ or } \text{V}_{\text{IN}} \leq \text{V}_{\text{IL}}, \text{f = f}_{\text{MAX}} \end{aligned}$		30	mA
I _{SB2}	Automatic CE power-down current — CMOS inputs	Max V_{CC} , \overline{CE}_1 , $\overline{CE}_3 \ge V_{CC} - 0.3 \text{ V}$, $CE_2 \le 0.3 \text{ V}$, $V_{IN} \ge V_{CC} - 0.3 \text{ V}$, or $V_{IN} \le 0.3 \text{ V}$, f = 0		25	mA

Capacitance

Tested initially and after any design or process changes that may affect these parameters.

Parameter	Description	Test Conditions	Max	Unit
C _{IN}	Input capacitance	$T_A = 25 ^{\circ}\text{C}$, f = 1 MHz, $V_{CC} = 3.3 \text{V}$	8	pF
C _{OUT}	IO capacitance		10	pF

Thermal Resistance

Tested initially and after any design or process changes that may affect these parameters.

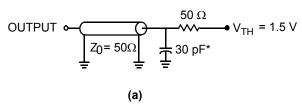
Parameter	Description	Test Conditions	119-Ball PBGA	Unit
Θ_{JA}		Still air, soldered on a 3 × 4.5 inch, four layer printed circuit board	20.31	°C/W
$\Theta_{\sf JC}$	Thermal resistance (junction to case)		8.35	°C/W

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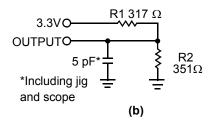
^{2.} V_{IL} (min) = -2.0 V and V_{IH} (max) = V_{CC} + 2 V for pulse durations of less than 20 ns.
3. \overline{CE}_{1} refers to a combination of \overline{CE}_{1} , \overline{CE}_{2} , and \overline{CE}_{3} . \overline{CE} is active LOW when \overline{CE}_{1} is LOW, \overline{CE}_{2} is HIGH, and \overline{CE}_{3} is LOW. \overline{CE} is HIGH when \overline{CE}_{1} is HIGH or \overline{CE}_{2} is LOW or \overline{CE}_{3} is HIGH.

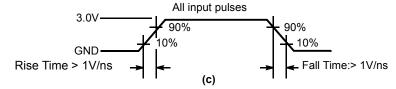


AC Test Loads and Waveform [4]



*Capacitive Load consists of all components of the test environment





AC Switching Characteristics

Over the operating range [5]

Parameter	Description	-	-10		
Parameter	Description	Min	Max	Unit	
Read Cycle	•				
t _{power} [6]	V _{CC} (Typical) to the first access	100	-	μS	
t _{RC}	Read cycle time	10	-	ns	
t _{AA}	Address to data valid	_	10	ns	
t _{OHA}	Data hold from address change	3	-	ns	
t _{ACE}	CE active LOW to data valid [3]	_	10	ns	
t _{DOE}	OE LOW to data valid	_	5	ns	
t _{LZOE}	OE LOW to low Z ^[7]	1	_	ns	
t _{HZOE}	OE HIGH to high Z [7]	_	5	ns	
t _{LZCE}	CE active LOW to low Z [3, 7]	3	_	ns	
t _{HZCE}	CE deselect HIGH to high Z [3, 7]	_	5	ns	
t _{PU}	CE active LOW to power-up [3, 8]	0	-	ns	
t _{PD}	CE deselect HIGH to power-down [3, 8]	_	10	ns	

Notes

- Valid SRAM operation does not occur until the power supplies reach the minimum operating V_{DD} (3.0 V). 100 µs (t_{power}) after reaching the minimum operating V_{DD}, normal SRAM operation begins including reduction in V_{DD} to the data retention (V_{CCDR}, 2.0 V) voltage.
 Test conditions assume signal transition time of 3 ns or less, timing reference levels of 1.5 V, and input pulse levels of 0 to 3.0V. Test conditions for the read cycle use output loading as shown in part a) of the AC Test Loads and Waveform (4), unless specified otherwise.

- tpower gives the minimum amount of time that the power supply is at typical V_{CC} values until the first memory access is performed. thzoe, thzoe, thzoe, thzoe, thzoe, thzoe, thzoe, thzoe, thzoe, thzoe are specified with a load capacitance of 5 pF as in part (b) of AC Test Loads and Waveform [4]. Transition is measured ±200 mV from steady state voltage. 7.
- 8. These parameters are guaranteed by design and are not tested.



AC Switching Characteristics (continued)

Over the operating range [5]

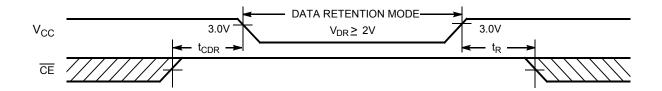
Downwater	Description	_	-10		
Parameter	Description	Min	Max	Unit	
Write Cycle [9, 10, 13]			•	•	
t _{WC}	Write cycle time	10	_	ns	
t _{SCE}	CE active LOW to write end [3]	7	_	ns	
t _{AW}	Address setup to write end	7	_	ns	
t _{HA}	Address hold from write end	0	_	ns	
t _{SA}	Address setup to write start	0	_	ns	
t _{PWE}	WE pulse width	7	_	ns	
t _{SD}	Data setup to write end	5.5	_	ns	
t _{HD}	Data hold from write end	0	_	ns	
t _{LZWE}	WE HIGH to low Z [7]	3	_	ns	
t _{HZWE}	WE LOW to high Z [7]	_	5	ns	

Data Retention Characteristics

Over the operating range

Parameter	Description	Conditions ^[3]	Min	Тур	Max	Unit
V_{DR}	V _{CC} for data retention		2	_	_	V
I _{CCDR}	Data retention current ^[9]	$V_{CC} = 2 \text{ V}, \overline{CE}_1, \overline{CE}_3 \ge V_{CC} - 0.2 \text{ V}, \\ CE_2 \le 0.2 \text{ V}, V_{IN} \ge V_{CC} - 0.2 \text{ V or } V_{IN} \le 0.2 \text{ V}$	_	_	25	mA
t _{CDR} [11]	Chip deselect to data retention time		0	_	_	ns
t _R ^[12]	Operation recovery time		t _{RC}	_	_	ns

Figure 2. Data Retention Waveform



Notes

- The internal write time of the memory is defined by the overlap of $\overline{\text{CE}}_1$ LOW, $\overline{\text{CE}}_2$ HIGH, $\overline{\text{CE}}_3$ LOW, and $\overline{\text{WE}}$ LOW. Chip enables must be active and $\overline{\text{WE}}$ must be LOW to initiate a write and the transition of any of these signals terminates the write. The input data setup and hold timing are referenced to the leading edge of the signal that terminates the write.
- 10. The minimum write cycle time for Write Cycle No. 3 ($\overline{\text{WE}}$ controlled, $\overline{\text{OE}}$ LOW) is the sum of t_{HZWE} and t_{SD} .
- 11. Tested initially and after any design or process changes that may affect these parameters.
 12. Full device operation requires linear V_{CC} ramp from V_{DR} to V_{CC(min)} ≥ 50 µs or stable at V_{CC(min)} ≥ 50 µs.

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Switching Waveforms

Figure 3. Read Cycle No. 1 (Address Transition Controlled) [13, 14]

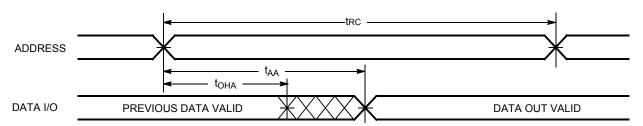


Figure 4. Read Cycle No. 2 (OE Controlled) [3, 14, 15]

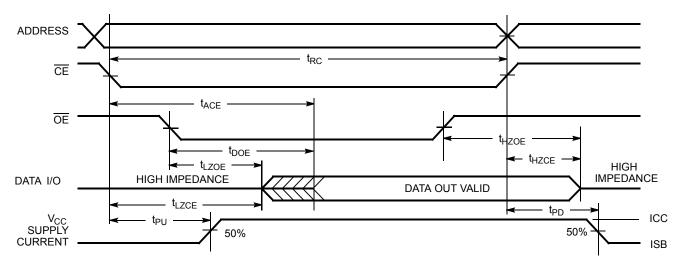
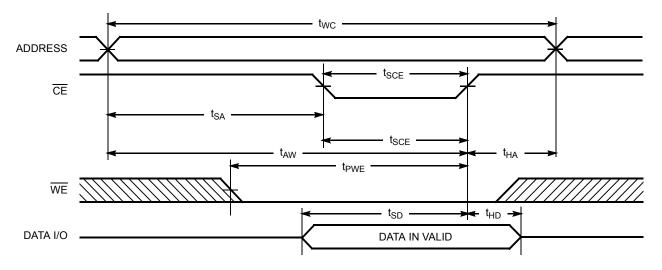


Figure 5. Write Cycle No. 1 (CE Controlled) [3, 16, 17]



Notes

- 13. <u>Device</u> is continuously selected. OE, CE = V_{IL}.

 14. WE is HIGH for read cycle.

 15. Address valid before or similar to CE transition LOW.

 16. Data IO is high impedance if OE = V_{IL}.

 17. If CE goes HIGH simultaneously with WE going HIGH, the output remains in a high impedance state.

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Switching Waveforms (continued)

Figure 6. Write Cycle No. 2 (WE Controlled, OE HIGH During Write) [3, 16, 17]

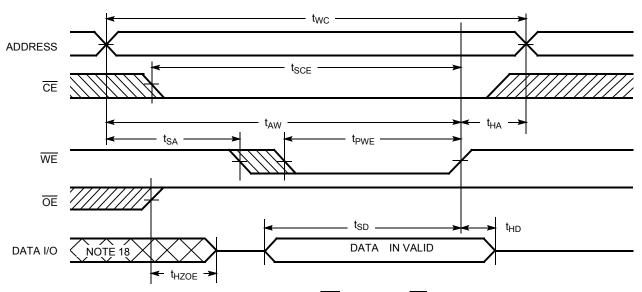
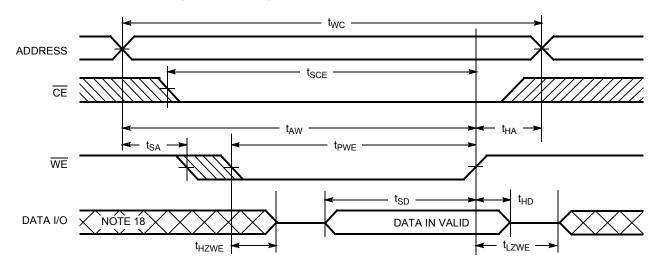


Figure 7. Write Cycle No. 3 ($\overline{\text{WE}}$ Controlled, $\overline{\text{OE}}$ LOW) [3, 17, 19]



Truth Table

CE ₁	CE ₂	CE ₃	OE	WE	IO ₀ -IO ₂₃	Mode	Power
Н	Х	Х	Χ	Х	High Z	Power-down	Standby (I _{SB})
Х	L	Х	Х	Х	High Z	Power-down	Standby (I _{SB})
Х	Х	Н	Χ	Х	High Z	Power-down	Standby (I _{SB})
L	Н	L	L	Н	Full Data Out	Read	Active (I _{CC})
L	Н	L	Х	L	Full Data In	Write	Active (I _{CC})
L	Н	L	Н	Н	High Z	Selected, outputs disabled	Active (I _{CC})

note

^{18.} During this period, the IOs are in the output state and input signals are not applied.

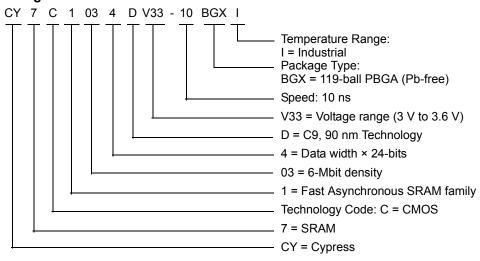
^{19.} The minimum write cycle pulse width should be equal to the sum of tSD and tHZWE.



Ordering Information

Speed (ns)	Ordering Code	Package Name	Package Type	Operating Range
10	CY7C1034DV33-10BGXI	51-85115	119-ball Plastic Ball Grid Array (14 x 22 x 2.4 mm) (Pb-free)	Industrial

Ordering Code Definitions

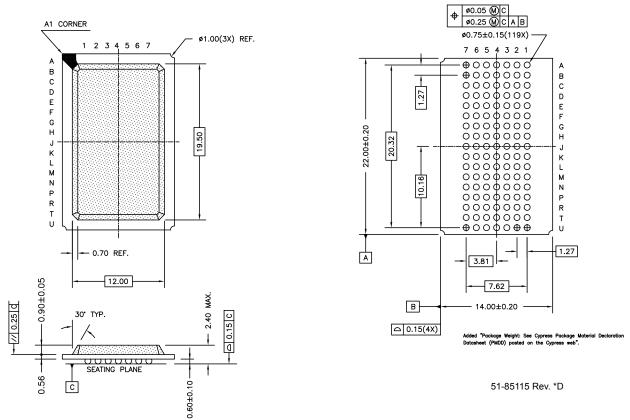


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Package Diagram

Figure 8. 119-ball PBGA (14 x 22 x 2.4 mm)





Acronyms

Acronym	Description
CMOS	complementary metal oxide semiconductor
I/O	input/output
SRAM	static random access memory
TSOP	thin small outline package
TTL	transistor-transistor logic

Document Conventions

Units of Measure

Symbol	Unit of Measure		
°C	degrees Celsius		
μΑ	microamperes		
mA	milliamperes		
MHz	megahertz		
ns	nanoseconds		
pF	picofarads		
V	volts		
Ω	ohms		
W watts			



Document History Page

Document Title: CY7C1034DV33 6-Mbit (256K X 24) Static RAM Document Number: 001-08351					
REV.	ECN NO.	Orig. of Change	Submission Date	Description of Change	
**	469517	NXR	See ECN	New data sheet	
*A	499604	NXR	See ECN	Added note 1 for NC pins Changed I_{CC} specification from 150 mA to 185 mA Updated Test Condition for I_{CC} in DC Electrical Characteristics table Added note for t_{ACE} , t_{LZCE} , t_{HZCE} , t_{PU} , t_{PD} , t_{SCE} in AC Switching Characteristics Table on page 4	
*B	1462586	VKN/SFV	See ECN	Converted from preliminary to final Updated block diagram Changed I _{CC} specification from 185 mA to 225 mA Updated thermal specs	
*C	2644842	VKN/PYRS	01/23/09	Replaced Commercial range with the Industrial Replaced 8 ns speed with 10 ns	
*D	3109199	PRAS	12/13/2010	Added Ordering Code Definitions. Updated Package Diagram.	
*E	3388455	TAVA	09/29/2011	Minor text edits. Added Acronyms and Document Conventions. Updated template.	
*F	4548836	MEMJ	10/22/2014	Updated Package Diagram: spec 51-85115 – Changed revision from *C to *D Completing Sunset Review.	
*G	4576478	MEMJ	11/21/2014	Added related documentation hyperlink in page 1. Added Note 19 in Switching Waveforms. Added note reference 19 in Figure 7.	

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